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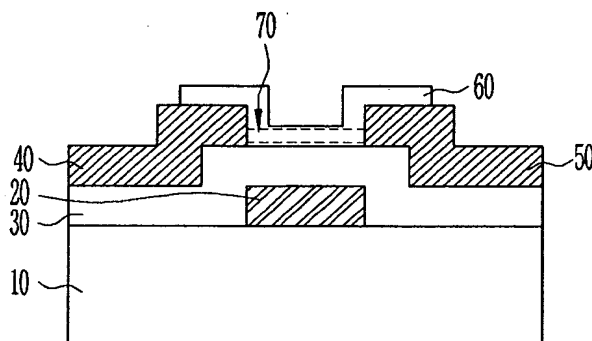
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(54) Title: METAL-INSULATOR TRANSITION SWITCHING TRANSISTOR AND METHOD FOR MANUFACTURING THE
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(57) Abstract: Provided is a metal-insulator-tran-
sition switching transistor with a gate electrode
on a silicon substrate (back-gate structure) and
a metal-insulator-transition channel layer of VO₂
that changes from an insulator phase to a metal
phase, or vice versa, depending on a variation of
an electric field, and a method for manufacturing
the same, whereby it is possible to fabricate a
metal-insulator-transition switching transistor
having high current gain characteristics and being
stable thermally.

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